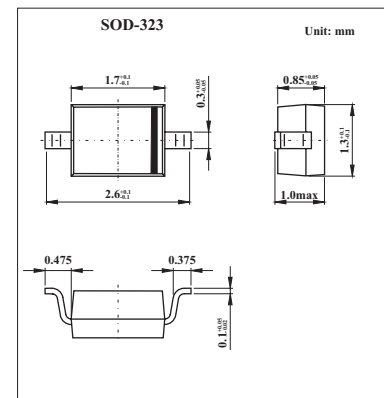


Schottky barrier diode

1PS76SB17

■ Features

- Low forward volatge
- Guard ring protected
- ESD > 500 V; Human body model
- Very small plastic SMD package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

PARAMATER	SYMBOL	MIN	MAX	UNIT
continuous reverse voltage	V_R		4	V
continuous forward current	I_F		30	mA
storage temperature	T_{stg}	-65	+150	$^\circ\text{C}$
junction temperature	T_j		100	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

PARAMATER	SYMBOL	CONDITIONS	TYP	MAX	UNIT
forward volatge	V_F	$I_F = 0.1 \text{ mA}$		300	mV
		$I_F = 1 \text{ mA}$	360	450	mV
		$I_F = 10 \text{ mA}$	470	600	mV
reverse current	I_R	$V_R = 3 \text{ V};$	0.15	0.25	μA
diode capacitance	C_d	$f = 1 \text{ MHz}; V_R = 0 \text{ V};$	0.8	1	pF
		$f = 1 \text{ MHz}; V_R = 0.5 \text{ V};$	0.65		pF
thermal resistance from junction to ambient	R_{th-j-a}	note 1		450	K/W

Note

1. Refer to SOD323 standard mounting conditions.

■ Marking

Marking	S7
---------	----